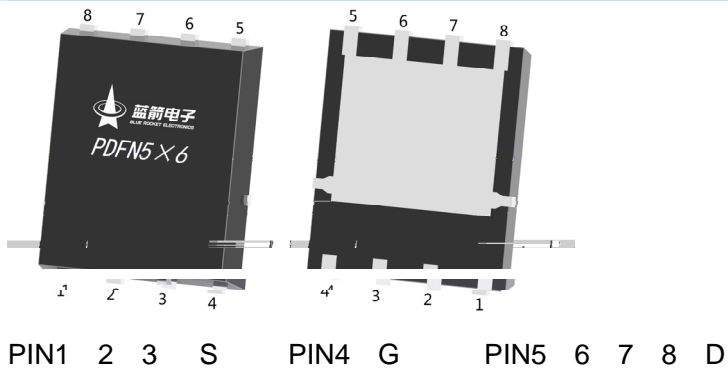
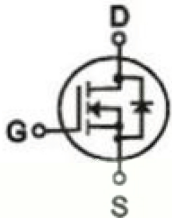


PDFN5 6 N  
N-Channel MOSFET in a PDFN5 6 Plastic Package.

Low  $R_{DS(ON)}$  to minimize conductive loss; low Gate Charge for fast switching; Low Thermal resistance; HF Product.

Battery Management.



See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Drain Current - Continuous	$I_D$	170	A
Drain Current – Pulsed	$I_{DM}$	340	A
Gate-Source Voltage	$V_{GS}$	20	V
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	65	W
Single Pulse Avalanche Energy(L=0.5mH)	$E_{AS}$	358	mJ
Avalanche Current(L=0.5mH)	$I_{AS}$	32	A
Junction and Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	
Thermal resistance, junction - case	$R_{JC}$	1.9	/ W
Thermal resistance, junction - ambient	$R_{JA}$	55	/ W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	40	46		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40\text{V}, V_{GS}=0\text{V}$			1.0	$\mu\text{A}$
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.9	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=10\text{A}$		1.2	1.5	m
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		2.0	2.5	
Input Capacitance	$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		4200		pF
Output Capacitance	$C_{oss}$			2000		
Reverse Transfer Capacitance	$C_{rss}$			120		
Gate resistance	$R_g$	$V_{GS}=0\text{V}, V_{DS}=0\text{V}$ $f=1\text{MHz}$		1.0		
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}, V_{DS}=20\text{V},$ $I_D=20\text{A}$		52		nC
Total Gate Charge	$Q_g(4.5\text{V})$			21		
Gate Source Charge	$Q_{gs}$			12		
Gate Drain Charge	$Q_{gd}$			5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}, V_{DS}=20\text{V},$ $R_L=1\Omega, R_{GEN}=3\Omega$		15		ns
Turn-On Rise Time	$t_r$			5.8		
Turn-Off Delay Time	$t_{d(off)}$			62		
Turn-Off Fall Time	$t_f$			10		

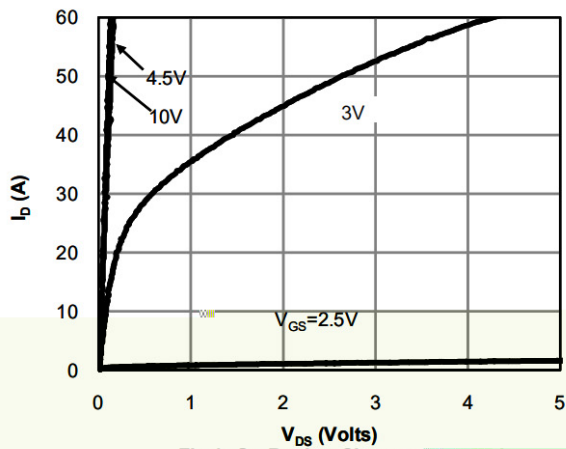


Figure 1: Power Characteristics

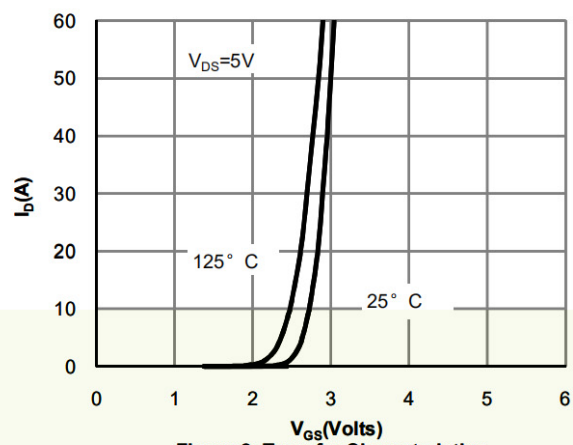


Figure 2: Transfer Characteristics

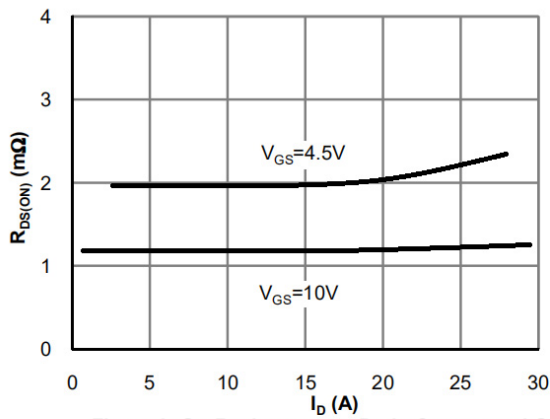


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

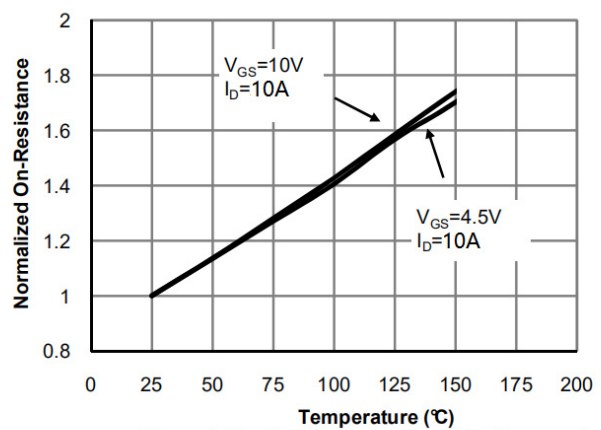


Figure 4: On-Resistance vs. Junction Temperature

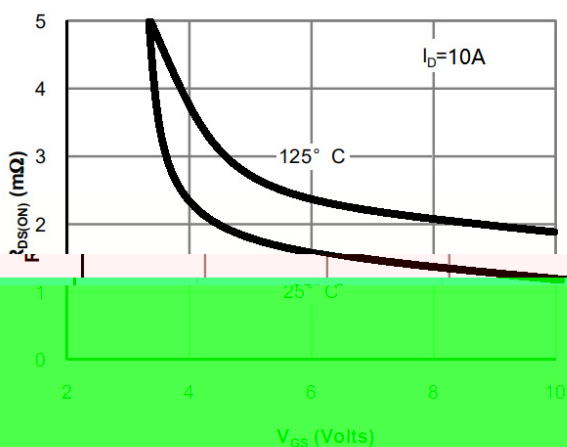


Figure 5: On-Resistance vs. Gate-Source Voltage

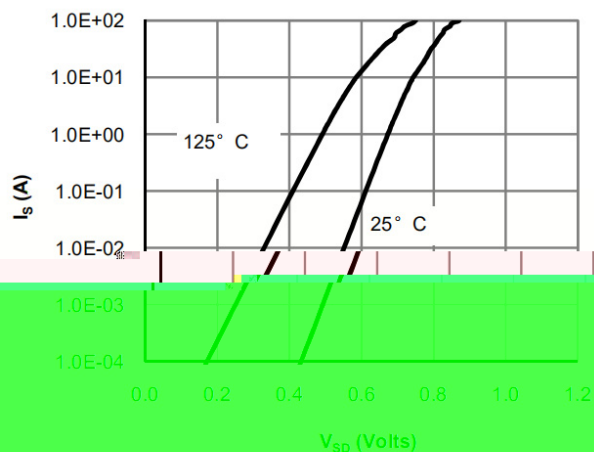


Figure 6: Body Diode Characteristics

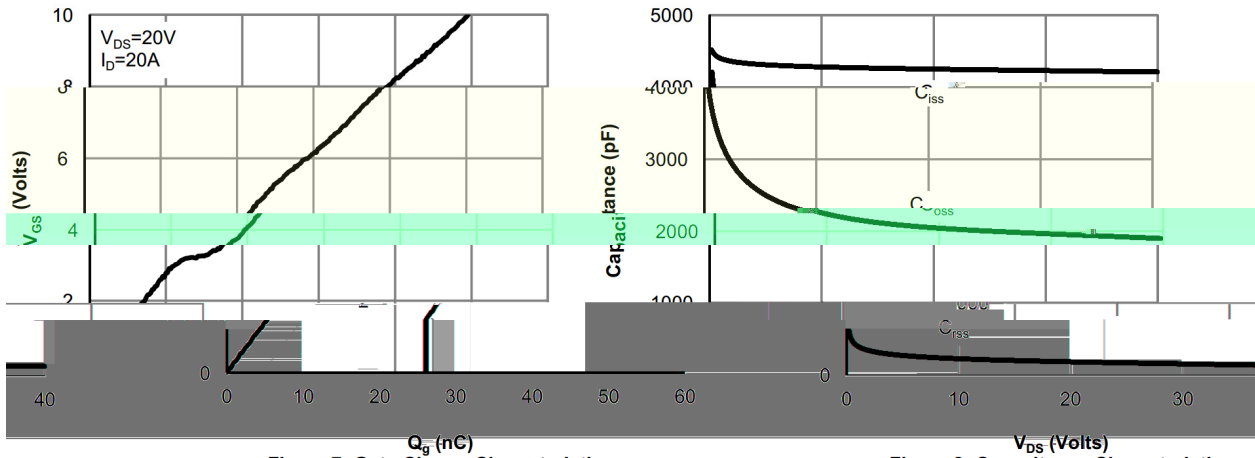


Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

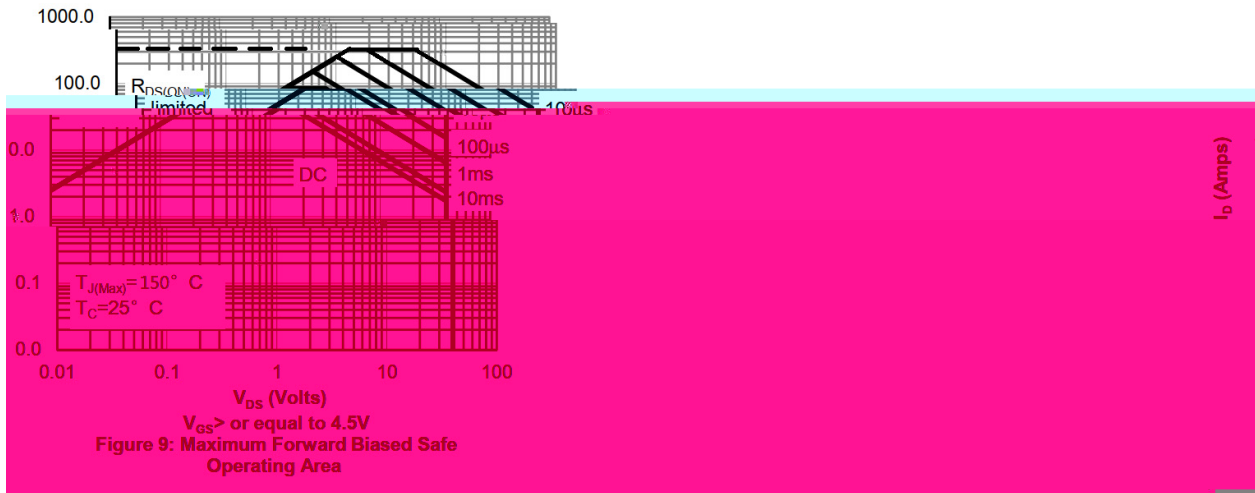


Figure 9: Maximum Forward Biased Safe Operating Area

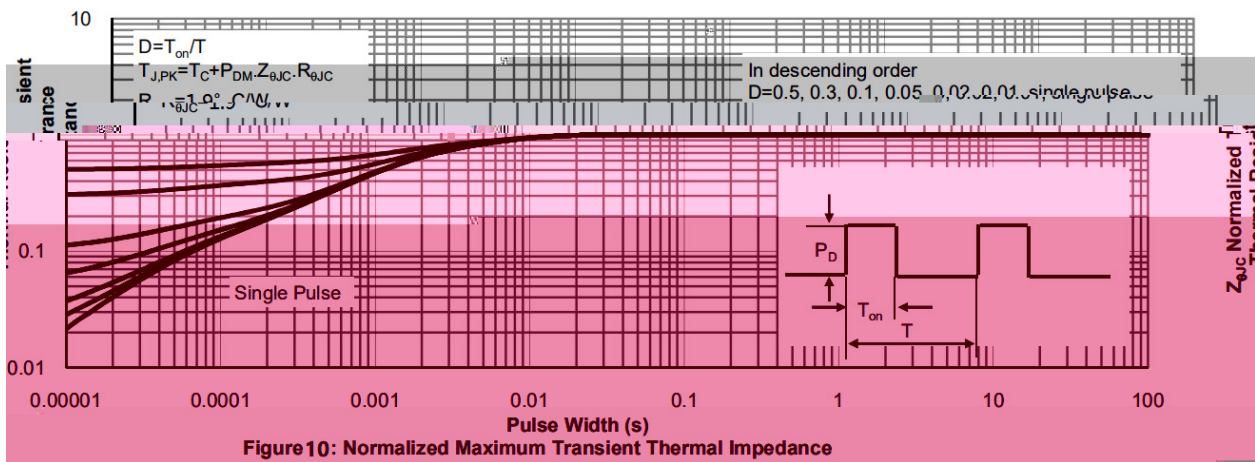
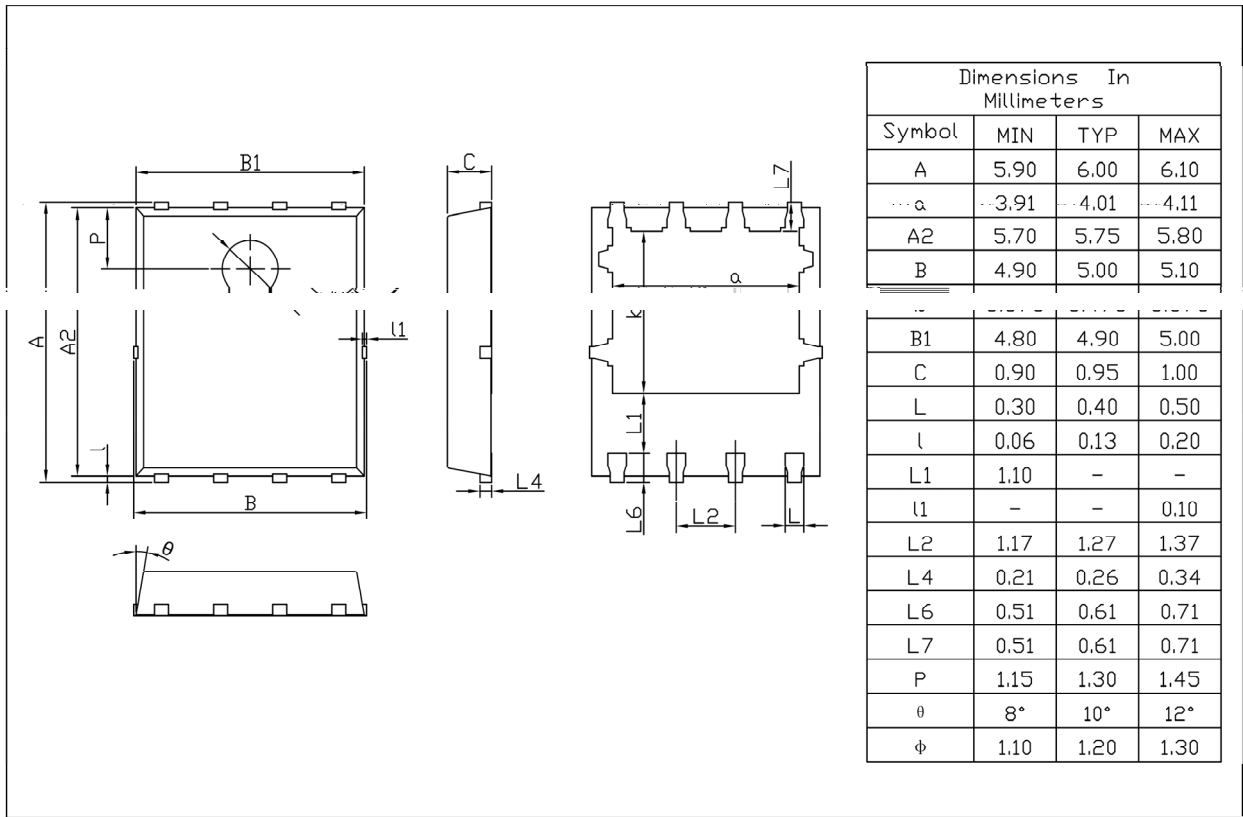


Figure 10: Normalized Maximum Transient Thermal Impedance

PDFN5 × 6

Unit:mm



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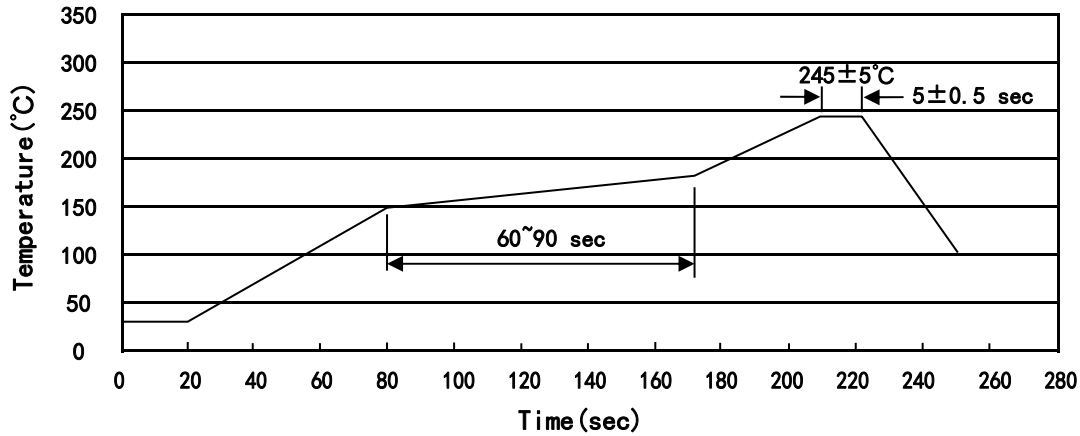
015N04S

Note

BR                    Company Code

015N04S            Product Type

\*\*\*\*.                Lot No. Code, code change with Lot No



Note:

- |   |     |     |    |          |   |
|---|-----|-----|----|----------|---|
| 1 | 150 | 180 | 60 | 90sec;   | 1.Preheating:150~180 , Time:60~90sec.   |
| 2 | 245 | 5   | 5  | 0.5sec;  | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 |     |     | 2  | 10 /sec. | 3. Cooling Speed: 2~10 /sec.            |

260 ±5                      10 ±1 sec.                      Temp.:260±5                      Time:10±1 sec

/ REEL

Package Type	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
PDFN5×6	5000	2	10000	6	60000	13"×12	360×360×50	380×335×366